



- ★ Super Low Gate Charge
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

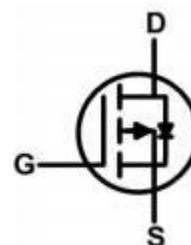
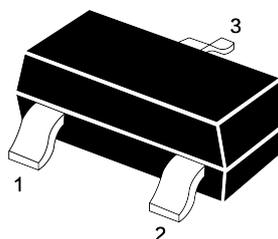
BVDSS	RDSON	ID
-20V	45mΩ	-3.5A

Description

The JH2305 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The JH2305 meet the RoHS and Green Product requirement with full function reliability approved.

SOT-23 Pin Configurations



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-3.5	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-3.0	A
I_{DM}	Pulsed Drain Current ²	-10	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ³	0.90	W
$P_D@T_A=70^\circ C$	Total Power Dissipation ³	0.54	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	120	°C/ W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ (t ≤10s)	---	95	°C/ W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.014	---	V/ °C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V, I _D =-4.9A	---	45	62	m
		V _{GS} =-2.5V, I _D =-3.4A	---	65	85	
		V _{GS} =-1.8V, I _D =-2A	---	---	---	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-0.4	---	-1.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	3.95	---	mV/ °C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-16V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-16V, V _{GS} =0V, T _J =55°C	---	---	-5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±12V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-3A	---	12.8	---	S
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-15V, V _{GS} =-4.5V, I _D =-3A	---	9.2	14.3	nC
Q _{gs}	Gate-Source Charge		---	1.89	2.6	
Q _{gd}	Gate-Drain Charge		---	3.1	4.3	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-10V, V _{GS} =-4.5V, R _G =3.3 Ω, I _D =-3A	---	5.6	11.2	ns
T _r	Rise Time		---	40.8	73	
T _{d(off)}	Turn-Off Delay Time		---	33.6	67	
T _f	Fall Time		---	18	36	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	757	1200	pF
C _{oss}	Output Capacitance		---	104	160	
C _{rss}	Reverse Transfer Capacitance		---	98	151	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	-3.5	A
I _{SM}	Pulsed Source Current ^{2,4}		---	---	-10	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1	V
t _{rr}	Reverse Recovery Time	I _F =-3A, di/dt=100A/μs, T _J =25°C	---	21.8	---	nS
Q _{rr}	Reverse Recovery Charge		---	6.9	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch²FR-4 board with 20Z copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

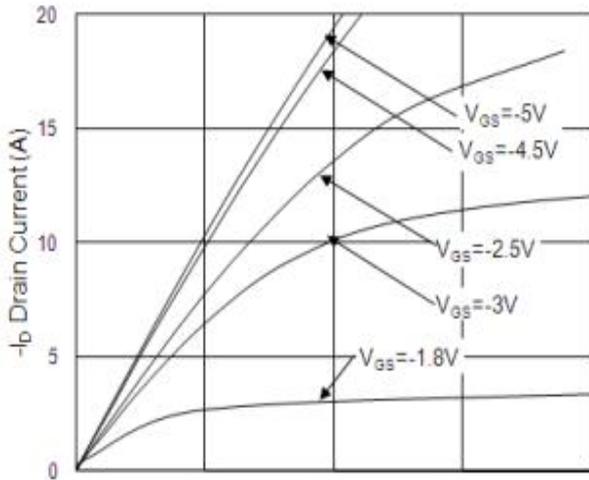


Fig. 1 Typical Output Characteristics

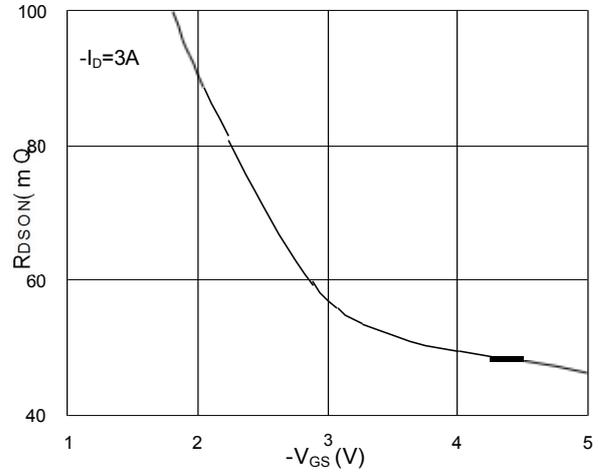


Fig. 2 On-Resistance vs. G-S Voltage

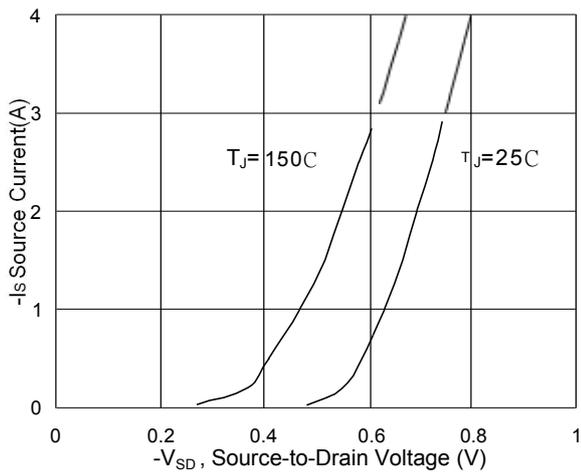


Fig. 3 Forward Characteristics of Reverse

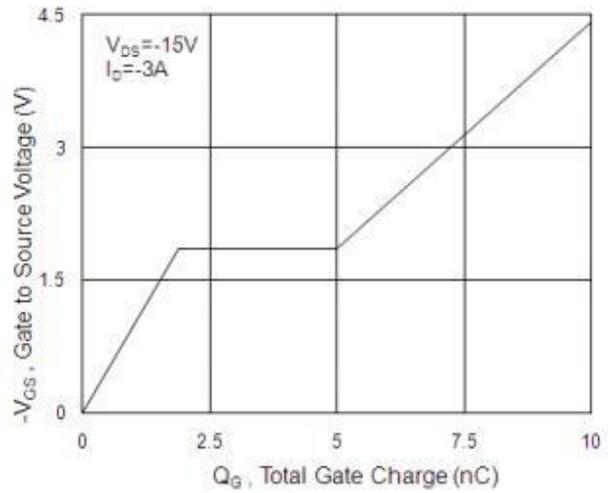


Fig. 4 Gate-charge Characteristics

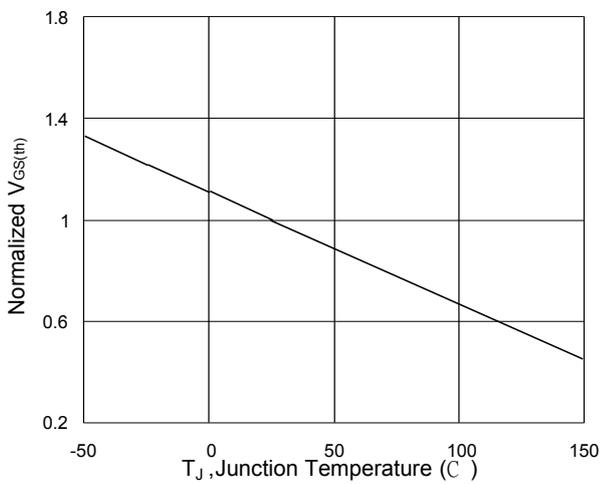


Fig. 5 Normalized $V_{GS(th)}$ vs. T_J

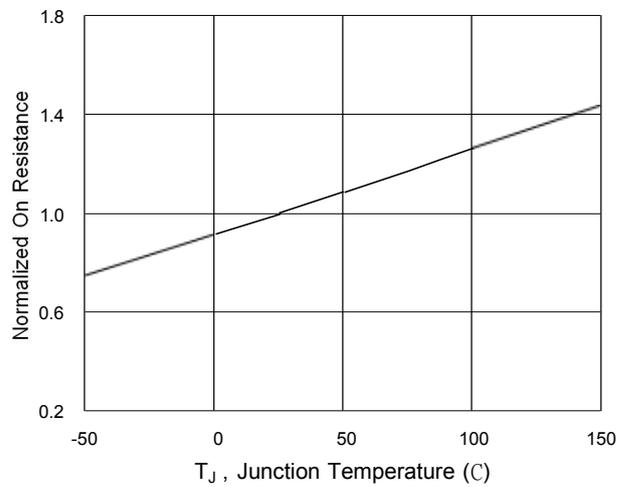


Fig. 6 Normalized $R_{DS(on)}$ vs. T_J

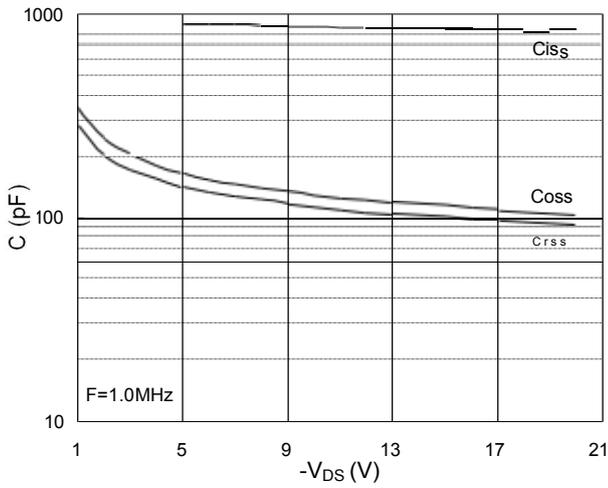


Fig. 7 Capacitance

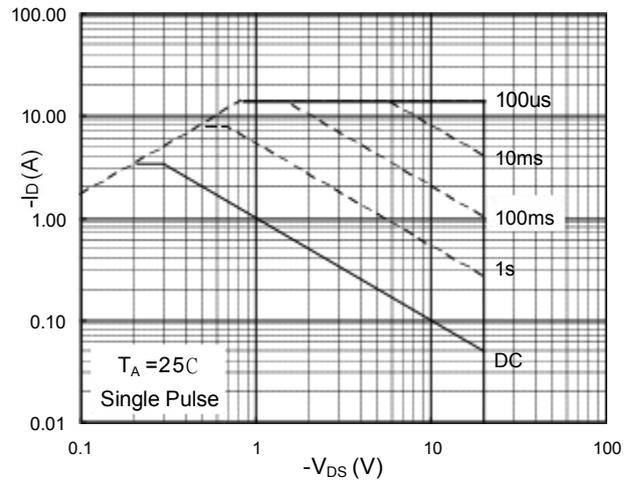


Fig. 8 Safe Operating Area

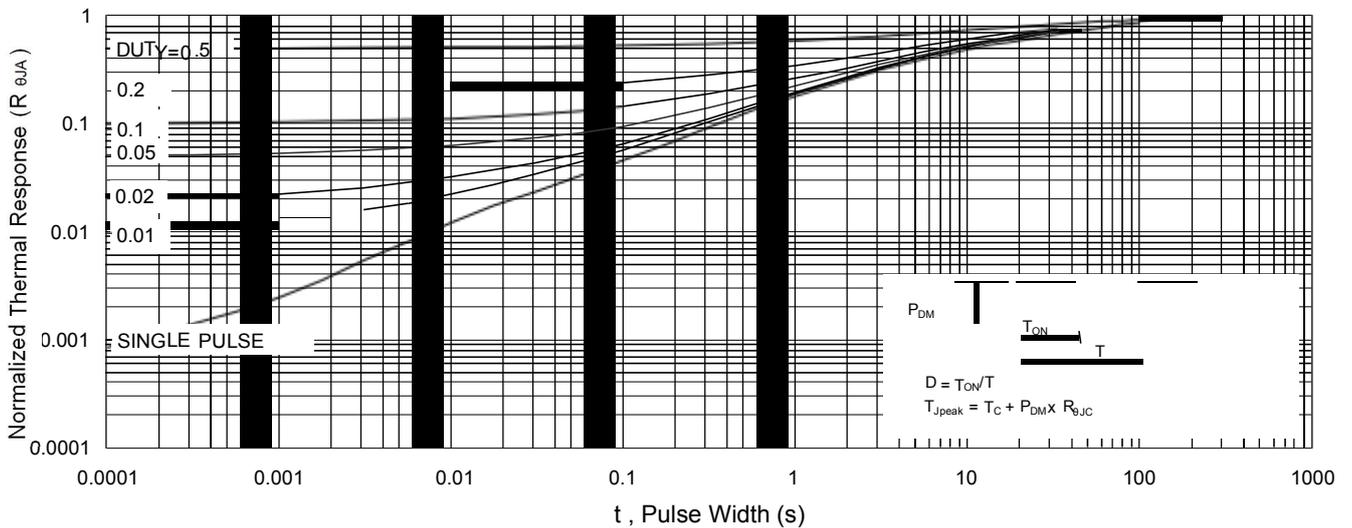


Fig. 9 Normalized Maximum Transient Thermal Impedance

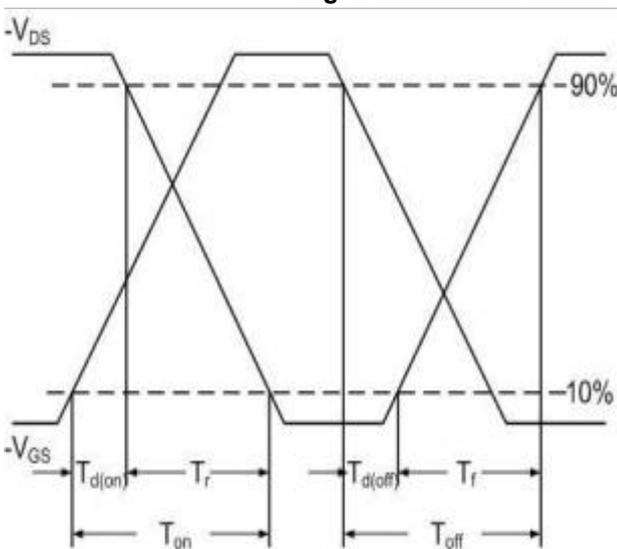


Fig. 10 Switching Time Waveform

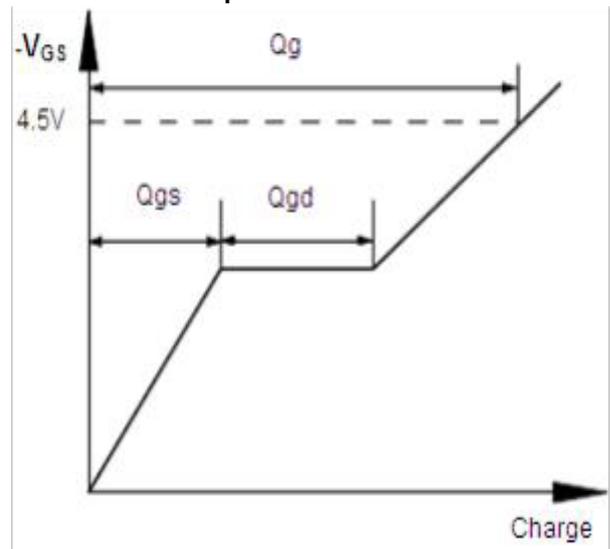
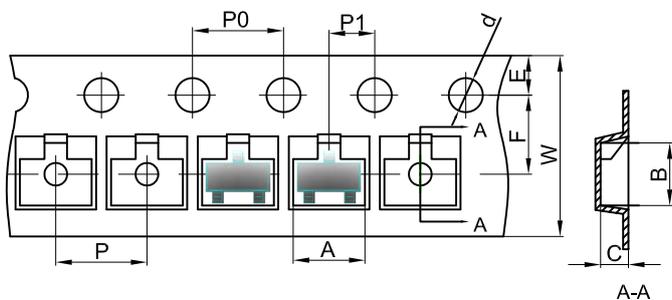


Fig. 11 Gate Charge Waveform

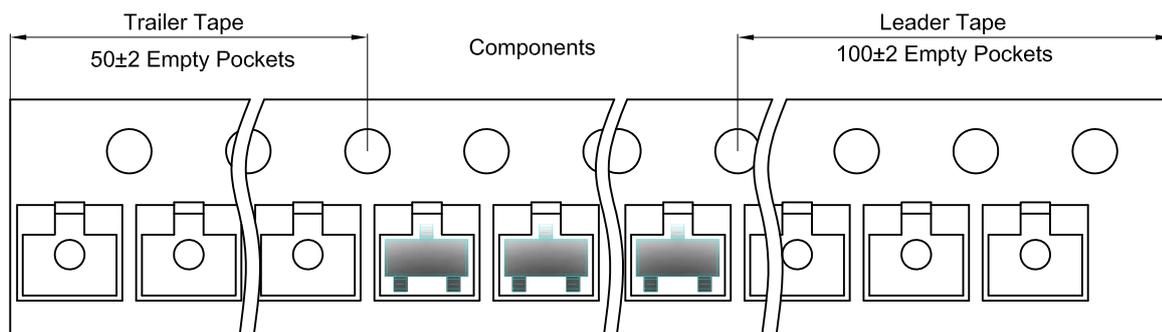
SOT-23 Tape and Reel

SOT-23 Embossed Carrier Tape

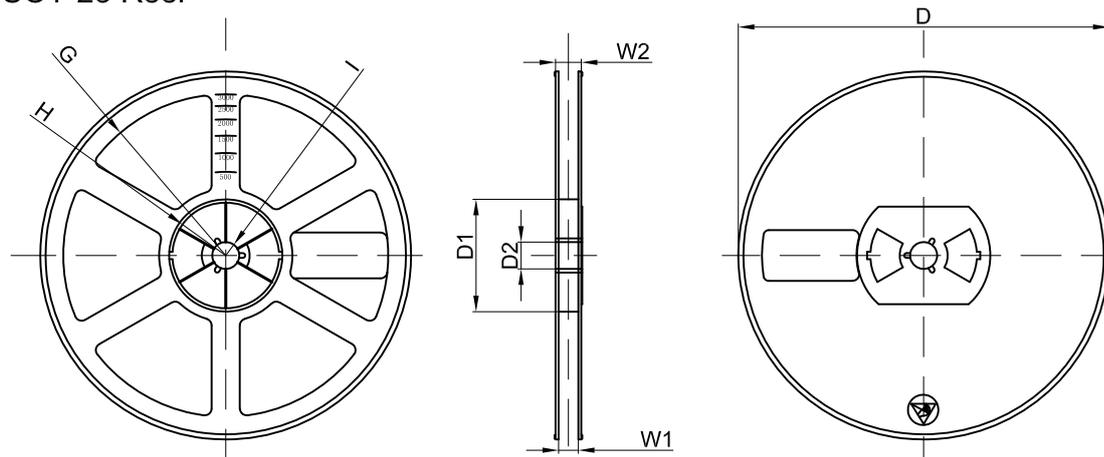


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23 Tape Leader and Trailer

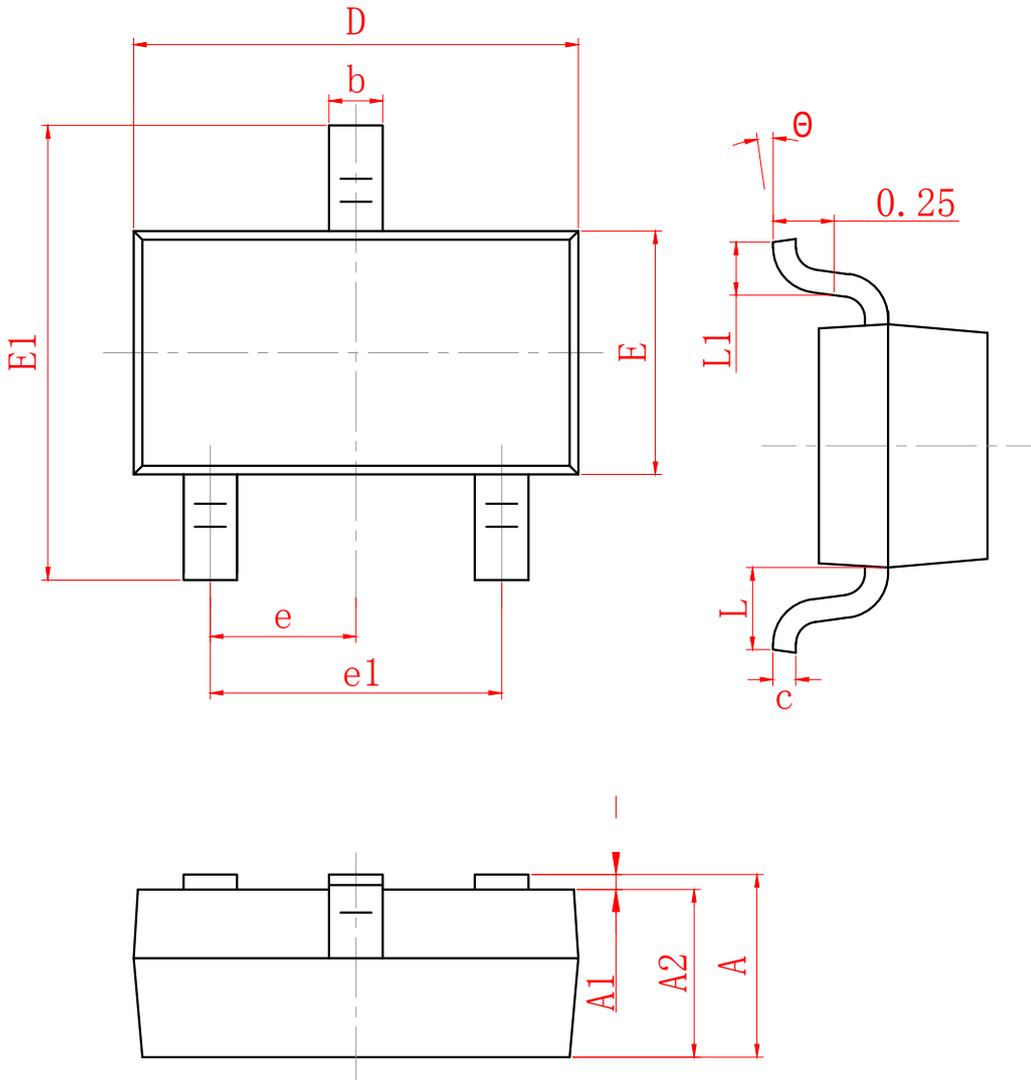


SOT-23 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	45,000 pcs	203×203×195	180,000 pcs	438×438×220	



SYMBOL	MILLIMETER	
	MIN	MAX
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950 TYP	
e1	1.800	2.000
L	0.550 REF	
L1	0.300	0.500
θ	0°	8°

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